

TRIGGER DIODES

DELIVERY

Antistatic film : 2500 devices per reel.

APPLICATIONS

Thyristors and triacs triggering.

ADVANTAGES

High reliability glass passivation insuring parameter stability and protection against junction contamination



MINIMELF
(Glass)

ABSOLUTE RATINGS (limiting values)

Symbol	Parameter	Value	Unit
P	Power Dissipation (1)	150	mW
I _{TRM}	Repetitive Peak on-state Current	2	A
T _{sig} T _J	Storage and Operating Junction Temperature Range	- 40 to 125 - 40 to 110	°C

THERMAL RESISTANCES

Symbol	Parameter	Value	Unit
R _{th} (j-a)	Junction-ambient (1)	400	°C/W
R _{th} (j-l)	Junction Tie-point	300	°C/W

(1) Mounted ceramic substrate of 10 mm x 10 mm x 0.6 mm.

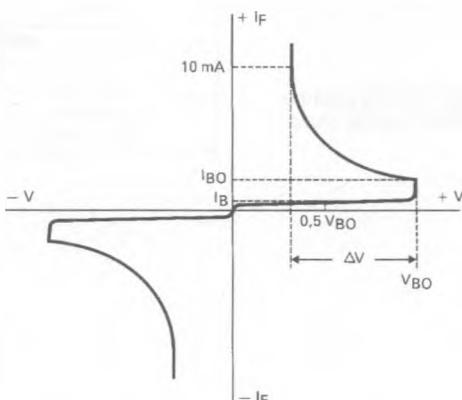
ELECTRICAL CHARACTERISTICS ($T_j = 25^\circ\text{C}$)

Symbol	Parameter	Test Conditions	Types	Min.	Typ.	Max.	Unit
V_{BO}	Breakover Voltage*	$C = 22 \text{ nF}^{**}$ See diagram 1	TMMDB3	28	32	36	V
$ (+V_{BO}) - (-V_{BO}) $	Breakover Voltage Symmetry	$C = 22 \text{ nF}^{**}$ See diagram 1				± 3	V
$ \Delta V \pm $	Dynamic Breakback Voltage*	$\Delta I = [I_{BO} \text{ to } I_F = 10 \text{ mA}]$ See diagram 1		5			V
V_O	Output Voltage*	See diagram 2		5			V
I_{BO}	Breakover Current*	$C = 22 \text{ nF}^{**}$				100	μA
t_r	Rise Time*	See diagram 3			1.5		μs
I_B	Leakage Current*	$V_B = 0.5 V_{BO} \text{ max}$ See diagram 1				10	μA

* Electrical characteristic applicable in both forward and reverse directions.

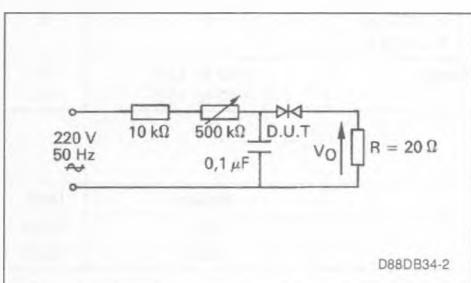
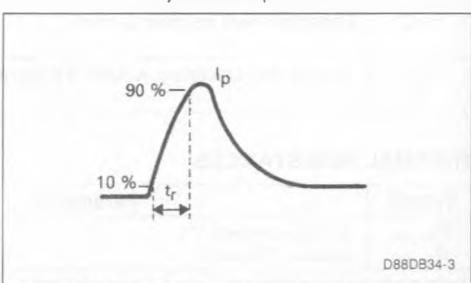
** Connected in parallel with the device.

DIAGRAM 1 : Current-voltage characteristics.



D88DB34-1

DIAGRAM 2 : Test circuit for output voltage.

DIAGRAM 3 : Test circuit see diagram 2.
Adjust R for $I_p = 0.5\text{A}$.

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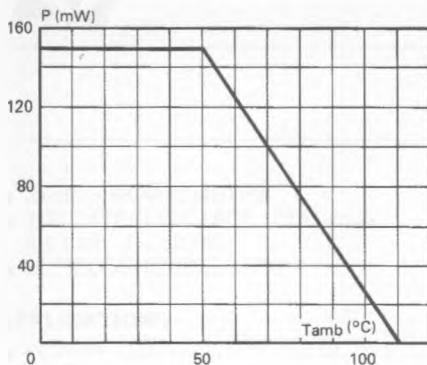


Fig. 1 - Power dissipation versus ambient temperature (maximum values).

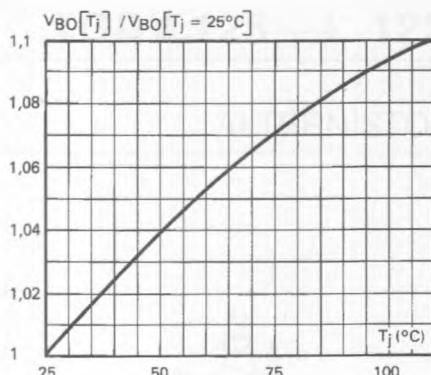


Fig. 2 - Relative variation of V_{BO} versus junction temperature (typical values).

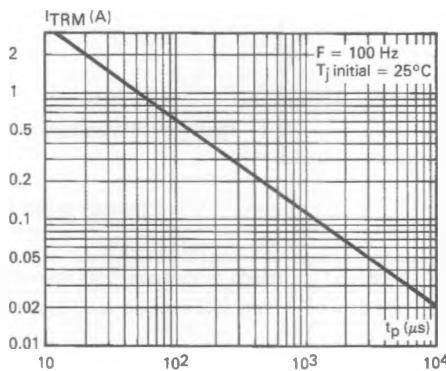


Fig. 3 - Peak pulse current versus pulse duration (maximum values).

PACKAGE MECHANICAL DATA

MINIMELF

